

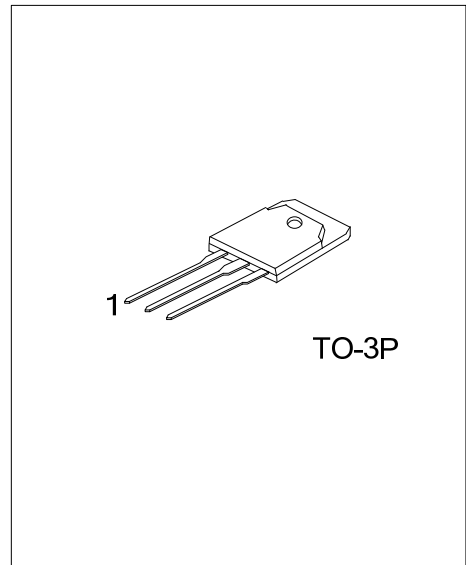


2SC4466

Preliminary

NPN EPITAXIAL SILICON TRANSISTOR

SILICON NPN TRIPLE DIFFUSED PLANAR TRANSISTOR



DESCRIPTION

The UTC **2SC4466** is a silicon NPN triple diffused planar transistor, it uses UTC's advanced technology to provide the customers with high DC current gain and high collector-base breakdown voltage, etc.

The UTC **2SC4466** is suitable for audio and general purpose, etc.

FEATURES

- * High DC current gain
- * High collector-base breakdown voltage

ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SC4466L-x-T3P-T	2SC4466G-x-T3P-T	TO-3P	B	C	E	Tube

Note: Pin Assignment: B: Base C: Collector E: Emitter

<p>2SC4466L-x-T3P-T</p> <p>(1) Packing Type (2) Package Type (3) Rank (4) Lead Free</p>	<p>(1) T: Tube (2) T3P: TO-3P (3) x: reference to Classification of h_{FE} (4) L: Lead Free, G: Halogen Free</p>
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■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	6	A
Base Current	I_B	3	A
Collector Power Dissipation ($T_C=25^\circ\text{C}$)	P_C	60	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ 150	$^\circ\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

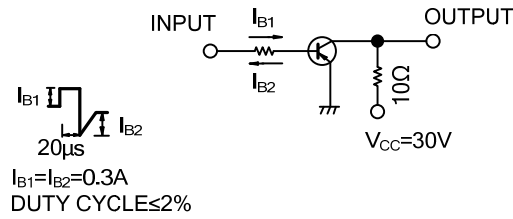
■ ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cut-Off Current		I_{CBO}	$V_{CB}=120\text{V}$			10	μA
Emitter Cut-Off Current		I_{EBO}	$V_{EB}=6\text{V}$			10	μA
Collector-Emitter Breakdown Voltage		BV_{CEO}	$I_C=50\text{mA}$	80			V
DC Current Gain		h_{FE}	$V_{CE}=4\text{V}, I_C=2\text{A}$	50		180	
Collector-Emitter Saturation Voltage		$V_{CE(SAT)}$	$I_C=2\text{A}, I_B=0.2\text{A}$			1.5	V
Current Gain Bandwidth Product		f_T	$V_{CE}=12\text{V}, I_E=-0.5\text{A}$		20		MHz
Output Capacitance		C_{ob}	$V_{CB}=10\text{V}, f=1\text{MHz}$		110		pF
Switching time	Turn-on time	t_{ON}	$V_{CC}=30\text{V}, R_L=10\Omega, I_C=3\text{A},$ $I_{B1}=0.3\text{A}, I_{B2}=0.3\text{A}$		0.16		μS
	Storage time	t_S			2.60		μS
	Fall time	t_F			0.34		μS

■ CLASSIFICATION OF h_{FE}

RANK	O	P	Y
RANGE	50~100	70~140	90~180

■ TEST CIRCUIT



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